

TECHNICAL DATA

PNP SILICON SMALL SIGNAL TRANSISTOR

Qualified per MIL-PRF-19500/392

Devices

2N3485A

2N3486A

Qualified Level

JAN JANTX JANTXV

Ratings	Symbol	2N3485A 2N3486A	Unit	
Collector-Emitter Voltage	V _{CEO}	60	Vdc	
Collector-Base Voltage	V _{CBO}	60	Vdc	*
Emitter-Base Voltage	V _{EBO}	5.0	Vdc	
Collector Current Continuous	I _C	600	mAdc	
Total Power Dissipation @ $T_A = +25^0 C^{(1)}$ @ $T_C = +25^0 C^{(2)}$	P _T	0.4 2.0	W W	
Operating & Storage Junction Temperature Range	T _J , T _{stg}	-55 to +200	⁰ C	
THERMAL CHARACTERISTICS				TO 46
Characteristics	Symbol	Max.	Unit	TO-46
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	0.439	⁰ mC/W	(TO-2064
Junction-to-Case	$R_{\theta JC}$	87	⁰ C/W	

2) Derate linearly 11.43 mW/ 0 C above T_C = +25 0 C



ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage	V	60		Vdc
$I_C = 10 \text{ mAdc}$	V _{(BR)CEO}	00		vuc
Collector-Base Cutoff Current				
$V_{CB} = 50 \text{ Vdc}$	I _{CBO}		10	ηAdc
$V_{CB} = 60 \text{ Vdc}$			10	μAdc
Emitter-Base Cutoff Current				
$V_{EB} = 3.5 \text{ Vdc}$	I _{EBO}		50	ηAdc
$V_{EB} = 5.0 \text{ Vdc}$			10	μAdc

2N3485A, 2N3486A JAN SERIES

Characteristics		Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽³⁾					
Forward-Current Transfer Ratio					
$I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	2N3485A 2N3486A		40 75		
$I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	2N3485A 2N3486A		40 100		
$I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	2N3485A 2N3486A	\mathbf{h}_{FE}	40 100	120	
$I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	2N3485A 2N3486A		40 100 40 50	120 300	
$I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	2N3485A 2N3486A				
Collector-Emitter Saturation Voltage					
$I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$		V _{CE(sat)}		0.4	Vdc
$I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$				1.6	
Base-Emitter Saturation Voltage					
$I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$		V _{BE(sat)}		1.3	Vdc
$I_{\rm C} = 500 \text{ mAdc}, I_{\rm B} = 50 \text{ mAdc}$				2.6	
DYNAMIC CHARACTERISTICS					
Small-Signal Forward Current Transfer R	atio				
$I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ k}$	Hz 2N3485A 2N3486A	^h fe	40 100		
Magnitude of Small-Signal Forward Current Transfer Ratio $I_C = 50 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$		^h fe	2.0	10	
Output Capacitance		G		8.0	ъĘ
$V_{CB} = 10$ Vdc, $I_E = 0$, 100 kHz $\le f \le 1.0$ MHz		C _{obo}		8.0	pF
Input Capacitance $V_{EB} = 2.0 \text{ Vdc}, I_C = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$		C _{ibo}		30	pF

(3) Pulse Test: Pulse Width = $300\mu s$, Duty Cycle $\leq 2.0\%$.

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